

# General Purpose Transistor



SMD Diodes Specialist

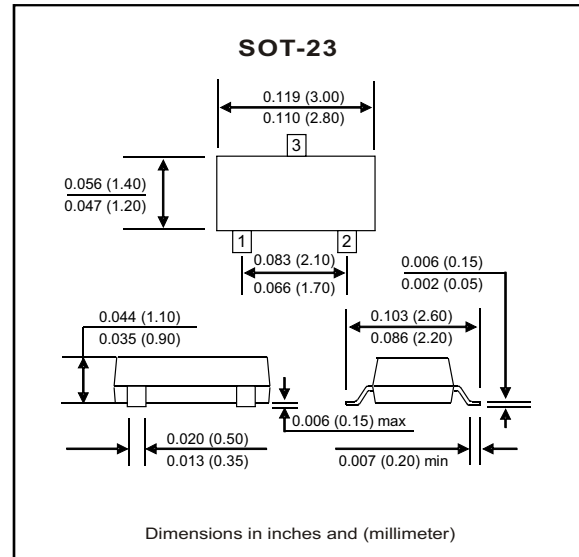
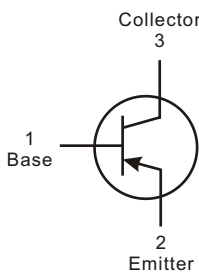
## MMBT3906-G (PNP)

RoHS Device



### Features

- Epitaxial planar die construction
- As complementary type, the NPN transistor MMBT3904-G is recommended



### Maximum Ratings (at $T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Min	Typ	Max	Unit
Collector-Base voltage	$V_{CB0}$			-40	V
Collector-Emitter voltage	$V_{CEO}$			-40	V
Emitter-Base voltage	$V_{EB0}$			-5	V
Collector current-Continuous	$I_C$			-0.2	A
Collector dissipation	$P_C$			0.3	W
Storage temperature and junction temperature	$T_{STG}, T_J$	-55		+150	$^{\circ}\text{C}$

### Electrical Characteristics (at $T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Conditions	Symbol	Min	Max	Unit
Collector-Base breakdown voltage	$I_C = -100\mu\text{A}, I_E = 0$	$V_{(BR)CB0}$	-40		V
Collector-Emitter breakdown voltage	$I_C = -1\text{mA}, I_B = 0$	$V_{(BR)CEO}$	-40		V
Emitter-Base breakdown voltage	$I_E = -100\mu\text{A}, I_C = 0$	$V_{(BR)EB0}$	-5		V
Collector cut-off current	$V_{CB} = -40\text{V}, I_E = 0$	$I_{CBO}$		-0.1	$\mu\text{A}$
Collector cut-off current	$V_{CE} = -40\text{V}, I_B = 0$	$I_{CEO}$		-0.1	$\mu\text{A}$
Emitter cut-off current	$V_{EB} = -5\text{V}, I_C = 0$	$I_{EBO}$		-0.1	$\mu\text{A}$
DC current gain	$V_{CE} = -1\text{V}, I_C = -10\text{mA}$	$h_{FE(1)}$	100	300	
	$V_{CE} = -1\text{V}, I_C = -50\text{mA}$	$h_{FE(2)}$	60		
Collector-Emitter saturation voltage	$I_C = -50\text{mA}, I_B = -5\text{mA}$	$V_{CE(sat)}$		-0.3	V
Base-Emitter saturation voltage	$I_C = -50\text{mA}, I_B = -5\text{mA}$	$V_{BE(sat)}$		-0.95	V
Transition frequency	$V_{CE} = -20\text{V}, I_C = -10\text{mA}$ $f = 100\text{MHz}$	$f_T$	250		Mhz
Delay time	$V_{CC} = -3.0\text{V}, V_{BE} = -0.5\text{V}$	$t_d$		35	nS
Rise time	$I_C = -10\text{mA}, I_{B1} = -1.0\text{mA}$	$t_r$		35	nS
Storage time	$V_{CC} = -3.0\text{V}_{dc}, I_C = -10\text{mA}$	$t_s$		225	nS
Fall time	$I_{B1} = I_{B2} = -1.0\text{mA}$	$t_f$		75	nS

## RATING AND CHARACTERISTIC CURVES (MMBT3906-G)

Fig.1 Capacitance

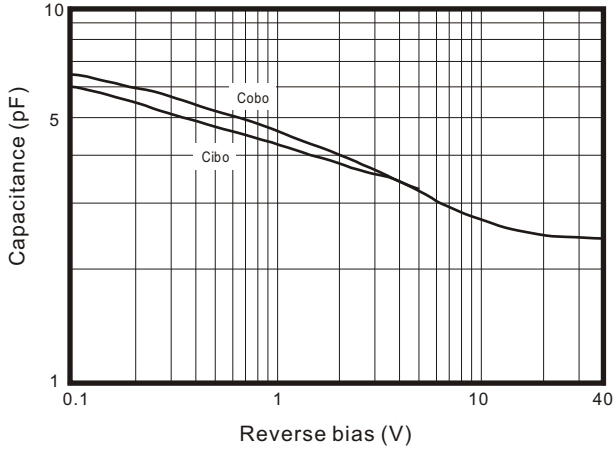


Fig. 2 - Charge data

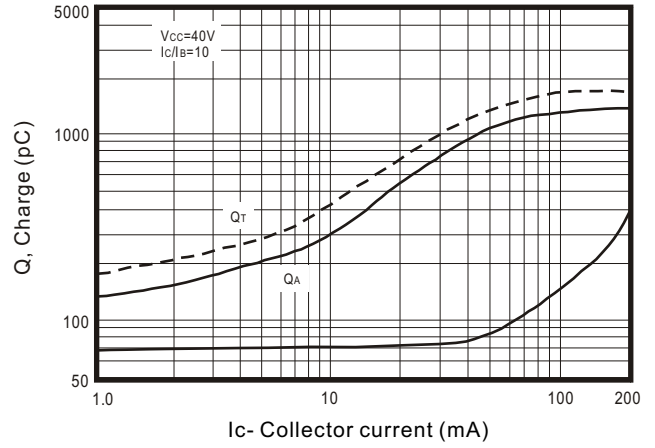


Fig. 3 - Turn-On Time

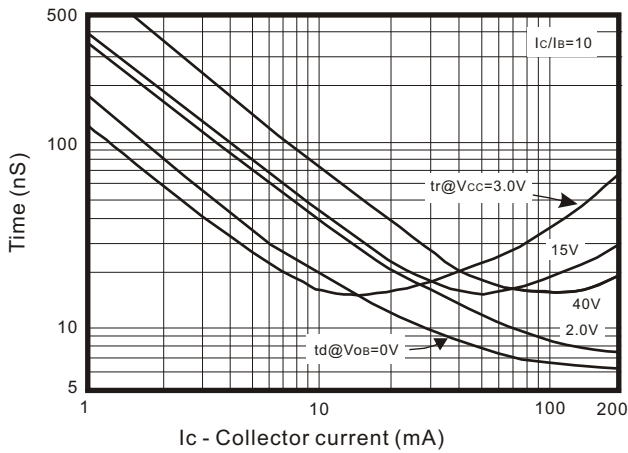


Fig. 4 - Fall time

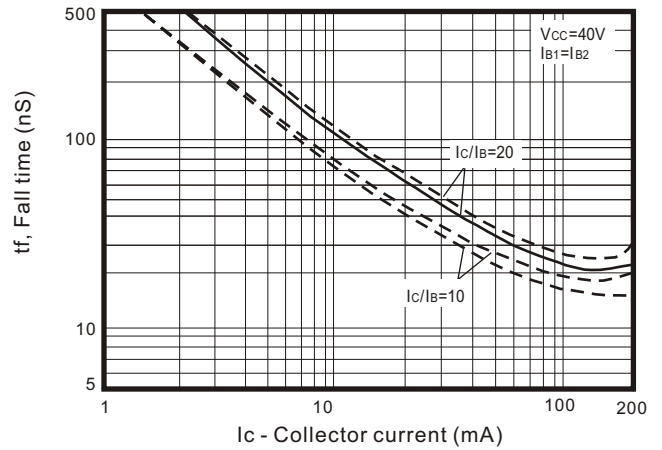


Figure 5

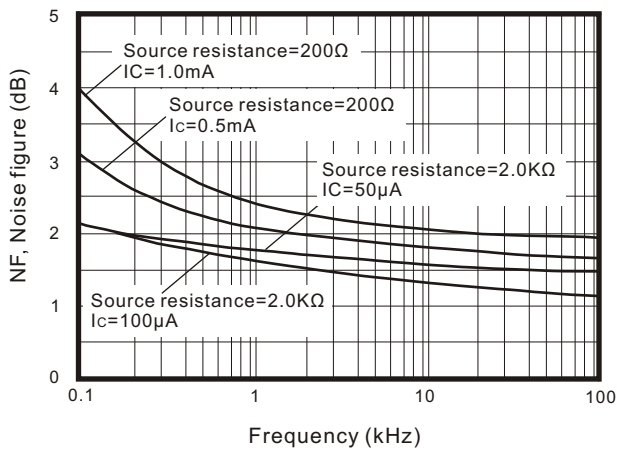
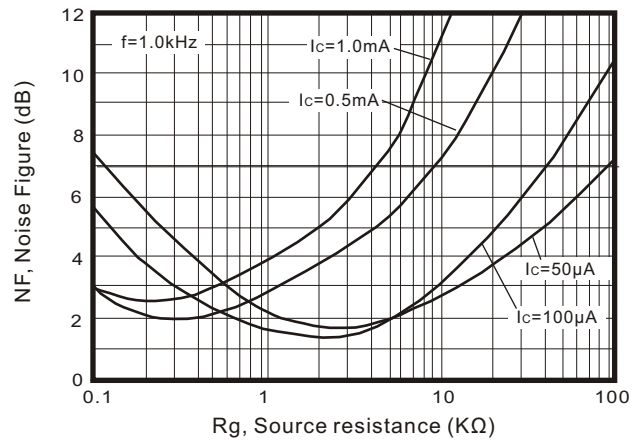


Figure 6



h Parameters ( $V_{CE} = -10V_{dc}$ ,  $f = 1.0kHz$ ,  $T_A = 25^\circ C$ )

Fig.7 Current gain

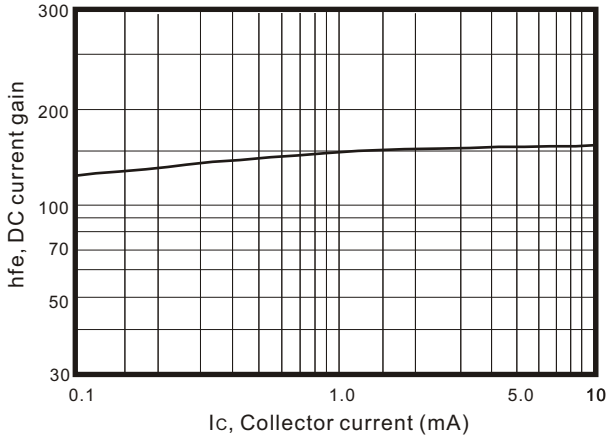


Fig. 8 - Output Admittance

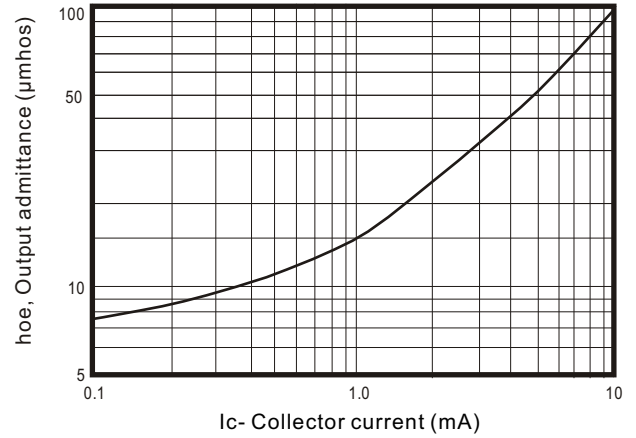


Fig. 9- Input impedance

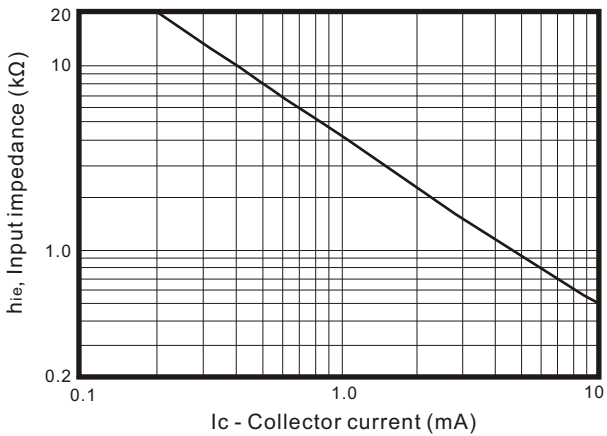


Fig. 10- Voltage feedback ratio

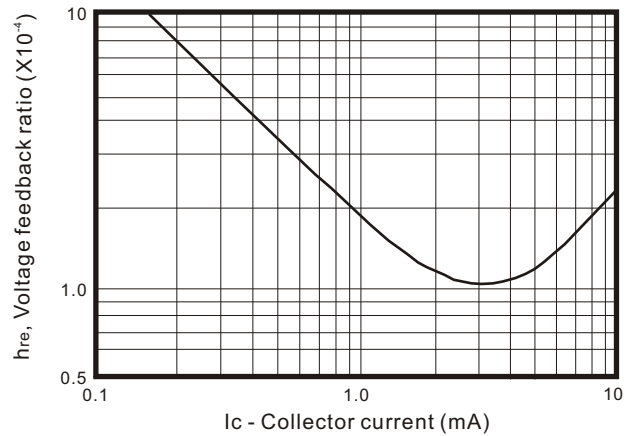


Fig. 11- "ON" voltages

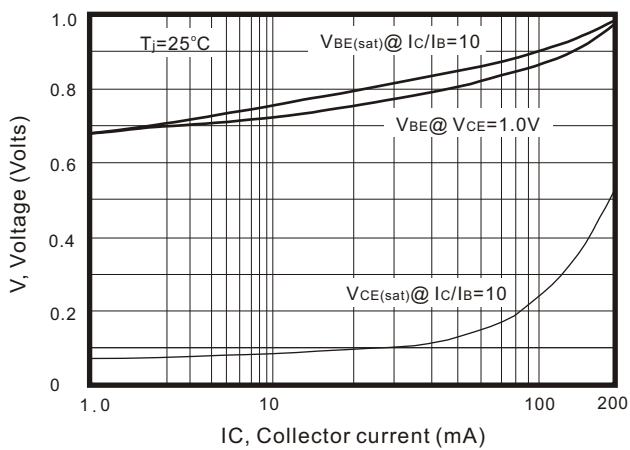


Fig. 12- Temperature coefficients

